Abstracts

A 2-18GHz Monolithic Variable Attenuator Using Novel Triple-Gate MESFETs

H.J. Sun and J. Ewan. "A 2-18GHz Monolithic Variable Attenuator Using Novel Triple-Gate MESFETs." 1990 MTT-S International Microwave Symposium Digest 90.2 (1990 Vol. II [MWSYM]): 777-780.

A monolithic variable attenuator requiring only a single positive external bias/drive voltage and capable of handling 0.4W input power has been developed using novel triple-gate MESFETs. The IC exhibits greater than 13dB attenuation and less than 2:1 VSWR from 2-18GHz with a maximum insertion loss of 2.7dB at 18GHz. It was developed from a lower power single-gate version using a unique scaling approach that preserves the circuit electrical property while enhancing the power handling almost nine-folds.

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